

The effect of temperature and excitation energy of the high- and low-spin $4f \rightarrow 5d$ transitions on charging of traps in $\text{Lu}_2\text{O}_3:\text{Tb},\text{M}$ ($\text{M} = \text{Ti}, \text{Hf}$)

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Rok wydania

2022

Czasopismo

Acta Materialia

Numer woluminu

231

Strony

117852/1-117852/9

DOI

10.1016/j.actamat.2022.117852

Kolekcja

Naukowa

Język

Angielski

Typ publikacji

Artykuł

Streszczenie

This work presents a fresh insight into the excited charges trapping in the $\text{Lu}_2\text{O}_3:\text{Tb},\text{M}$ ($\text{M} = \text{Ti}, \text{Hf}$) ceramics and their characteristics as storage and/or persistent luminescence phosphors. The results were obtained by applying an exceedingly versatile set of experiments based on thermoluminescence and thermoluminescence excitation spectroscopy and exposed a dual-nature of these materials. In the contrary to the previous research, here we found that at least some of these materials can generate efficient persistent luminescence due to the presence of shallow traps which can be charged only upon specific irradiation conditions – by the spin-forbidden $4f \rightarrow 5d$ transition of Tb^{3+} around 360 nm and, possibly, the ${}^7\text{F}_6 \rightarrow {}^5\text{D}_3$ intra-configurational transition of the activator at just slightly longer wavelengths. Besides that, changing the sample charging temperature the efficiency of filling the traps – both deep and shallow – with the 360 nm radiation varied greatly and exposed a very broad distribution of trap energies. Charging with 360 nm radiation at room temperature fills only the shallow traps giving, never reported in $\text{Lu}_2\text{O}_3:\text{Tb},\text{Ti}$ and $\text{Lu}_2\text{O}_3:\text{Tb},\text{Hf}$, intense persistent luminescence, while at higher temperatures the deep traps are filled. At any temperature, radiation of wavelengths < 320 nm fills almost exclusively deep traps responsible for TL at high temperatures, 230 °C in $\text{Lu}_2\text{O}_3:\text{Tb},\text{Hf}$ and 355 °C in $\text{Lu}_2\text{O}_3:\text{Tb},\text{Ti}$.

Słowa kluczowe

Luminescence, Defects, Thermally activated processes, Irradiation effect

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Adres publiczny

<http://dx.doi.org/10.1016/j.actamat.2022.117852>

Strona internetowa wydawcy

<http://www.elsevier.com>